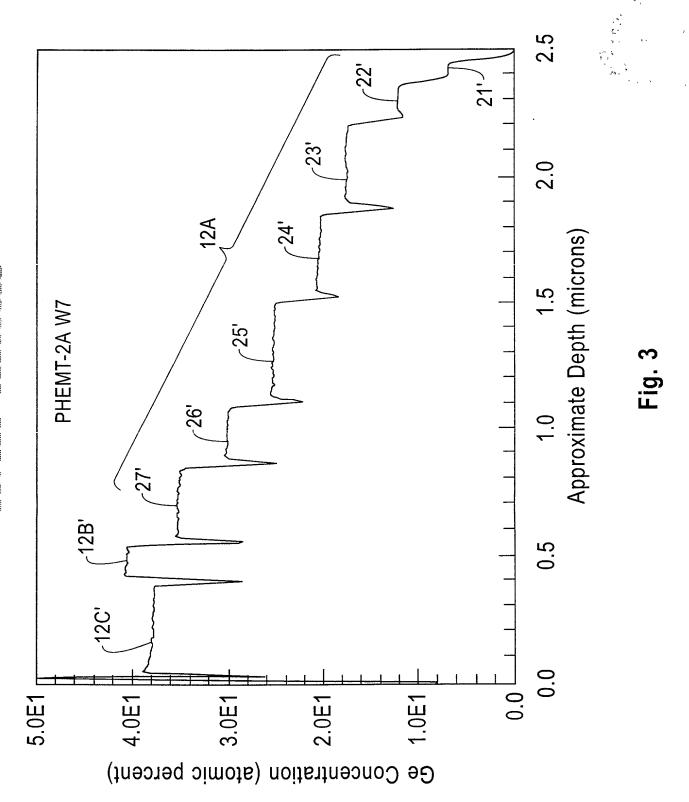
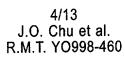


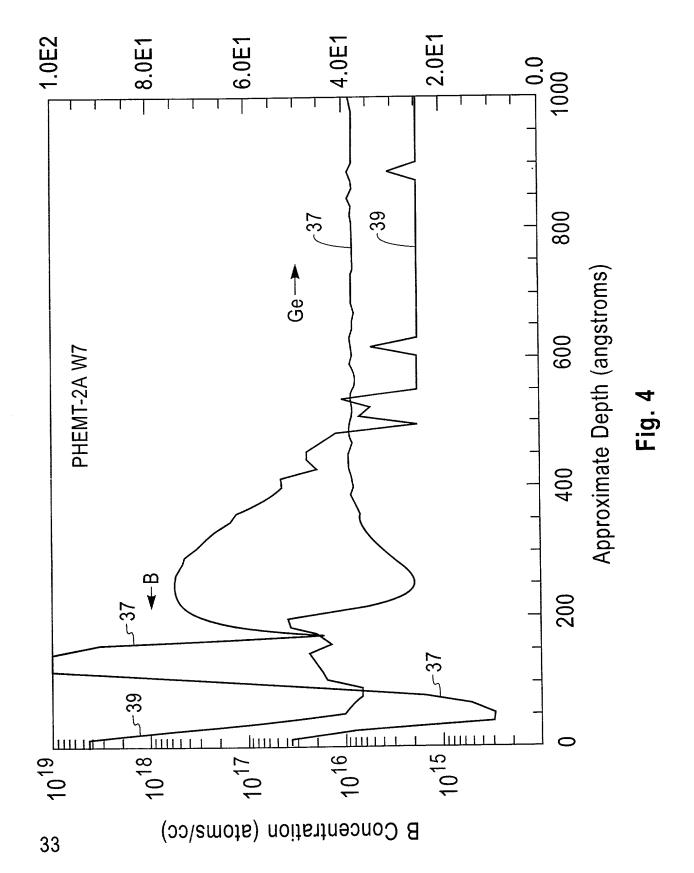
Fig. 1

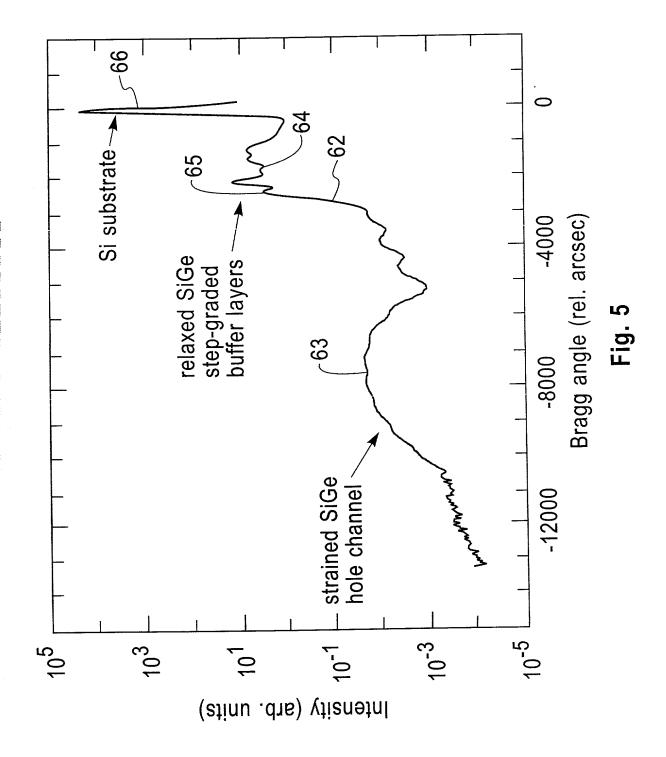
- Cap si and SiGe Device Layers Strain Relief Layers Silicon Substrate Thick Buffer XTEM of PHEMT 2.3 Structure 450 nm -11,31 -33 23' - 22' - 21' - 25' — 12B \_ 26' — 27' — 24' 12A <

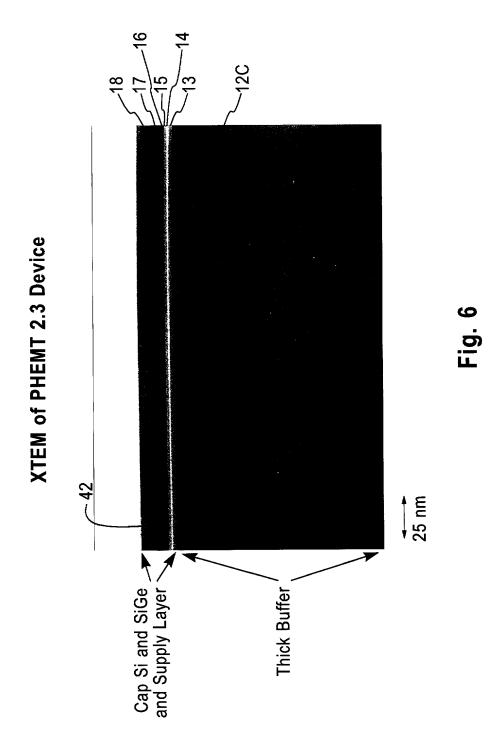
Fig. 2



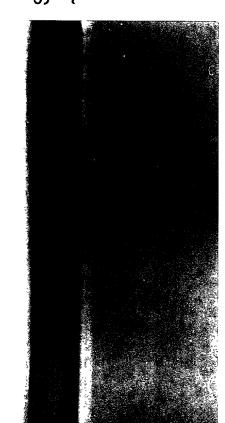








Stacking fault densities  $\sim 10^6$  -  $10^8$ /cm<sup>2</sup>



Fia. 7

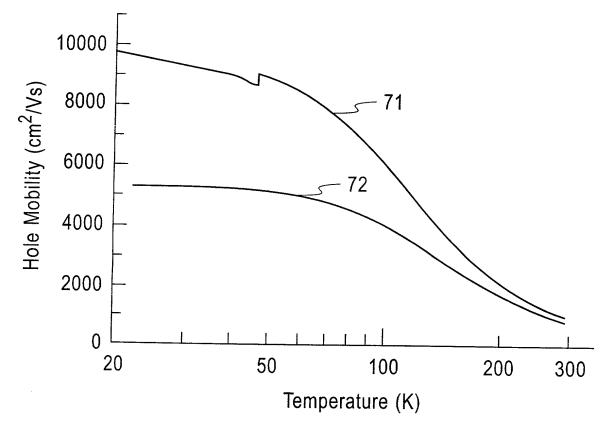


Fig. 8

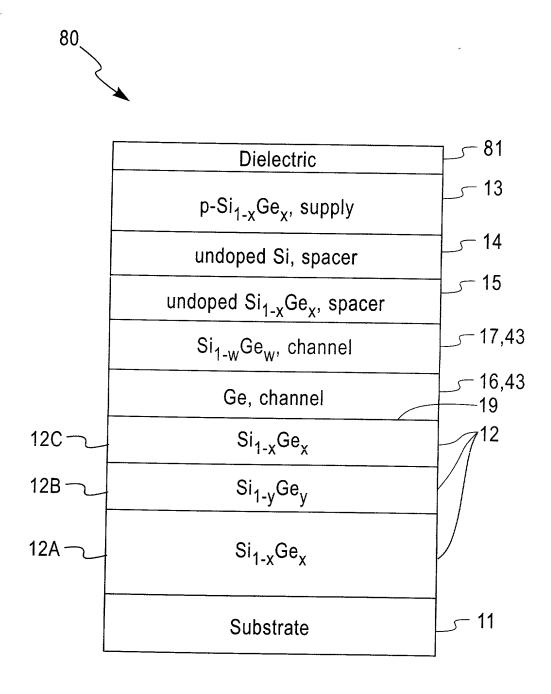
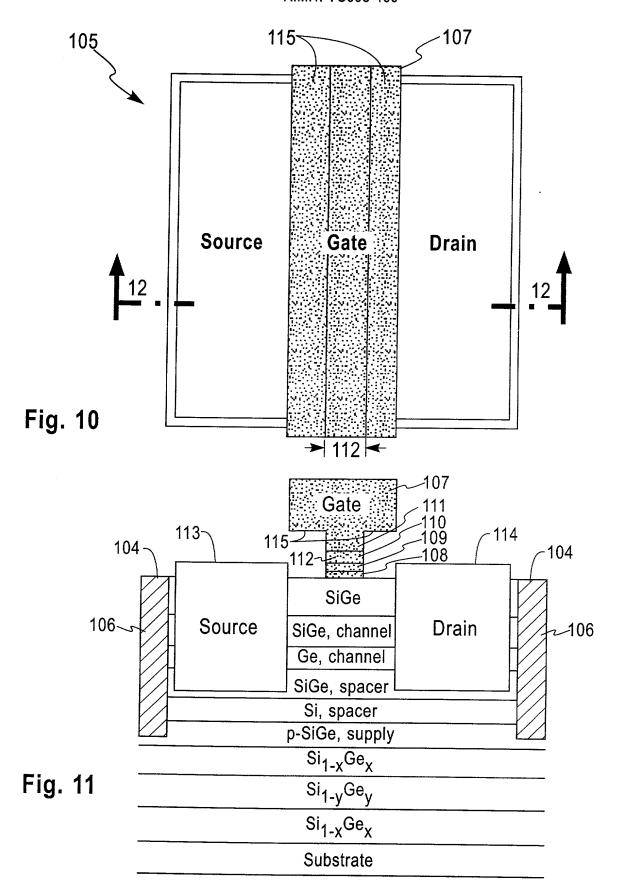


Fig. 9

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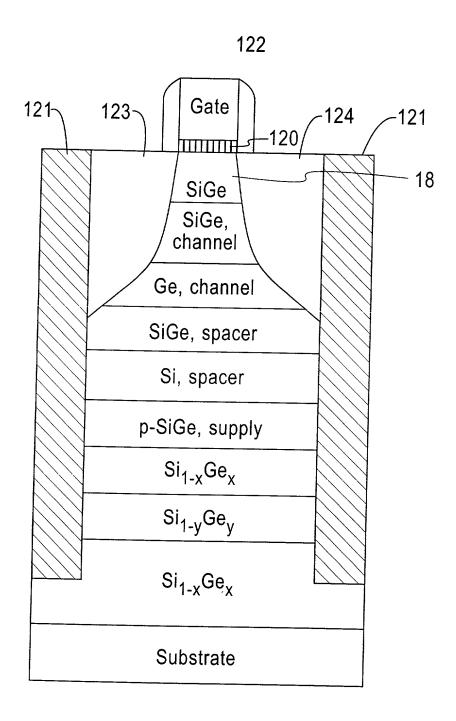


Fig. 12

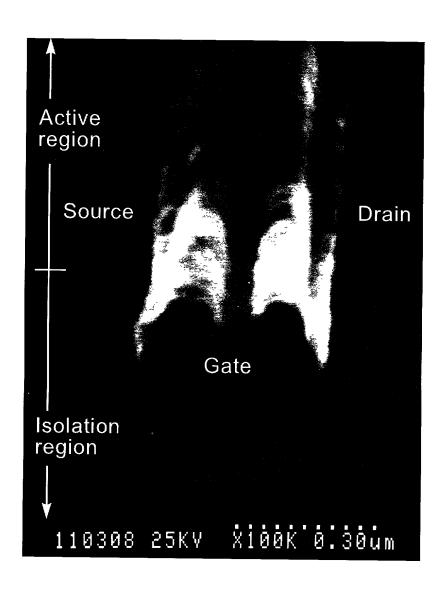


Fig. 13

p-type composite-channel MODFET,  $L_g$  = 0.09 $\mu$ m, W = 25 $\mu$ m

